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System and method using multilayer qubit lattice arrays for quantum computing

Abstract

A quantum computing (QC) system that includes a plurality of qubits arranged substantially in a plurality of substantially planar regions that are substantially parallel to one another, at least some of the substantially planar regions including two or more qubits and one or more qubits of each substantially planar region configured to interact with one or more qubits of at least one other substantially planar region.

Inventors: Hendrickson; Peter Carl (Reston, VA), Erwin; Jadon Daniel (Herndon, VA)

Applicant: Hendrickson; Peter Carl (Reston, VA); Erwin; Jadon Daniel (Herndon, VA)

Family ID: 1000008763127

Assignee: KBR WYLE SERVICES, LLC (N/A, N/A)

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Background/Summary

CROSS-REFERENCE TO RELATED APPLICATION (1) This application is a continuation of U.S. application Ser. No. 17/090,747, filed Nov. 5, 2020, which claims priority to Provisional Application Ser. No. 62/933,148 filed Nov. 8, 2019, the contents of which are hereby incorporated by reference in their entirety.

BACKGROUND

Field

(1) This application is generally directed to quantum computing (QC), and more particularly to quantum computer architectures employing lattice array structures of more than one dimension.

Description of the Related Art

(2) Technology paths toward scalable quantum computing have been diverse. Demonstrated performance in the various figures of merit vary widely according to the type of physical quantum bit (also referred to as a “qubit”) employed by each approach. Approaches based on either trapped ions or on superconducting qubits have consistently led the field through more than two decades.

SUMMARY

(3) Certain implementations disclosed herein provide a quantum computer architecture employing a lattice array structure of more than one dimension for implementing and interconnecting quantum gates in which more than two qubits can be simultaneously entangled. Certain implementations disclosed herein provide quantum microprocessor configuration and gate array design platforms for quantum processing chips, analogous to field programmable gate arrays (FPGAs) which can advantageously provide a degree of reconfigurability. Certain implementations disclosed herein provide quantum microprocessor configuration and gate array design platforms for quantum processing chips, analogous to application specific integrated circuits (ASICs) which can advantageously be optimized for a specified application and can advantageously provide custom design flexibility.

(4) Certain implementations disclosed herein comprise lattice configurations comprising multiple fully-connected qubits arranged as arrays of three-dimensional (3-D) lattice structures (e.g., cells), with simultaneous multi-qubit gate operations enabled by qubits arrayed in geometric layouts. For example, certain implementations can be configured as multiple two-dimensional (2-D) (e.g., planar) qubit arrays (e.g., layers) that are substantially parallel to one another and that form arrays of three-dimensional (3-D) cells. For another example, certain other implementations can be configured as multiple one-dimensional (1-D) (e.g., linear) qubit arrays (e.g., rows and columns; lattices; chains) that are substantially parallel to one another. In both of these examples, the arrays of cells can be analogized to or referred to as 3-D crystal structures. While various implementations are described herein as utilizing trapped ion qubits (e.g., in microchip structures) to illustrate the nature of quantum interactions to be utilized (e.g., optimized), other implementations can use one or more alternative qubit technologies.

(5) Certain implementations disclosed herein provide a quantum computing (QC) system comprising a plurality of qubits arranged substantially in a plurality of substantially planar regions

(e.g., planes; layers) that are substantially parallel to one another, at least some of the substantially planar regions comprising two or more qubits and one or more qubits of each substantially planar region configured to interact with one or more qubits of at least one neighboring substantially planar region. For example, the QC system can comprise a first substrate and a second substrate, the first substrate and the second substrate substantially parallel to one another, and the QC system can further comprise a multiple-qubit gate array comprising the plurality of qubits arranged as a plurality of multiple-qubit gates positioned in a region between the first substrate and the second substrate. The qubits of the multiple-qubit gate array can comprise surface electrode traps configured to contain ions (e.g., charged atoms; charged molecules) at or near a surface of at least one of the first and second substrates, and can be arranged substantially in a plurality of substantially planar regions (e.g., planes; layers; levels), with at least some of the qubits of at least one substantially planar region configured to interact (e.g., to be quantum-mechanically entangled) with at least some of the qubits of at least one other (e.g., neighboring) substantially planar region.

(6) Certain implementations disclosed herein provide a quantum computing (QC) system comprising a plurality of qubits arranged substantially in a plurality of linear arrays that are substantially parallel to one another, at least some of the linear arrays comprising two or more qubits and one or more qubits of each linear array configured to interact with one or more qubits of at least one neighboring linear array. For example, the QC system can comprise a multiple-qubit gate array comprising the plurality of qubits arranged as a plurality of multiple-qubit gates positioned in a region between two or more substrates. The qubits of the multiple-qubit gate array can comprise surface electrode traps configured to contain ions (e.g., charged atoms; charged molecules) at or near a surface of at least one of the substrates, and can be arranged substantially in a plurality of linear arrays, with at least some of the qubits of at least one linear array configured to interact (e.g., to be quantum-mechanically entangled) with at least some of the qubits of at least one other (e.g., neighboring) linear array.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

- (1) The accompanying drawings, which are incorporated in and constitute a part of this specification, illustrate one or more implementations described herein and, together with the description, explain these implementations.
- (2) FIGS. 1A-1C and 2A-2F schematically illustrate various aspects of example multiple-qubit gates (e.g., cells) in accordance with certain implementations described herein.
- (3) FIG. 3A schematically illustrates a top view of four example first portions (e.g., bases) of an example array comprising four multiple-ion qubit gates (e.g., cells) in accordance with certain implementations described herein.
- (4) FIG. 3B schematically illustrates a top view of four example second portions (e.g., caps) of the example array and four multiple-ion qubit gates in accordance with certain implementations described herein.
- (5) FIGS. 3C-3D schematically illustrate an exploded view and a top view, respectively, of the example array and four multiple-ion qubit gates of FIGS. 3A-3B in accordance with certain implementations described herein.
- (6) FIG. 3E schematically illustrate an exploded view of another example array with four ten-ion qubit gates in accordance with certain implementations described herein.
- (7) FIGS. 4A-4B schematically illustrate an exploded view and a top overlay view, respectively, of an example array comprising sixteen multiple-ion qubit gates in a 4×4 array in accordance with certain implementations described herein.
- (8) FIG. 4C schematically illustrates a top overlay view of another example multiple-ion qubit gate

array with sixteen multiple-ion qubit gates in accordance with certain implementations described herein.

(9) FIG. 4D schematically illustrates a top overlay view of another example multiple-ion qubit gate array comprising four multiple-ion qubit gates in accordance with certain implementation described herein.

(10) FIG. 4E schematically illustrates a top overlay view of another example multiple-ion qubit gate array comprising sixteen multiple-ion qubit gates in accordance with certain implementations described herein.

(11) FIGS. 4F-4G schematically illustrate an exploded view and a top overlay view, respectively, of another example array comprising sixteen multiple-ion qubit gates in a 4×4 array in accordance with certain implementations described herein.

(12) FIGS. 5A-5I schematically illustrate various views of portions of example QC structures in accordance with certain implementations described herein.

(13) FIG. 6A schematically illustrates a top overlay view of an example 4×4 array of alternating four-ion qubit gates and thirteen-ion qubit gates with a plurality of optical ports in accordance with certain implementations described herein.

(14) FIGS. 6B-6D schematically illustrate optical signals irradiating the ions of the array of FIG. 6A in accordance with certain embodiments described herein.

(15) FIG. 6E schematically illustrates top views of the base portions and an overlay of the base and cap portions of another example 4×4 array of ten-ion qubit gates with a plurality of ion loading holes and optical ports in accordance with certain implementations described herein.

(16) FIG. 6F schematically illustrates an overlay of the base and cap portions of another example 4×4 array of ten-ion qubit gates with a plurality of microwave antenna regions in accordance with certain implementations described herein.

(17) FIG. 7A schematically illustrates a side view of a portion of an example QC structure and FIG. 7B schematically illustrates a close-up view of a smaller portion of the QC structure of FIG. 7A in accordance with certain implementations described herein.

(18) FIGS. 7C and 7D schematically illustrate two views of another example QC structure in accordance with certain implementations described herein.

(19) FIG. 7E schematically illustrates ion loading holes and single-ion optical detectors in accordance with certain implementations described herein.

(20) FIG. 8 schematically illustrates a side view and a top projection view of an example QC structure having an example 16×16 cell array in accordance with certain implementations described herein.

(21) FIG. 9 shows four tables comparing the total number of qubits for various 4×4 cell arrays in accordance with certain implementations described herein.

DETAILED DESCRIPTION

Overview

(22) Certain implementations of the quantum computing (QC) system described herein advantageously provide a multilayer architecture to enable optimal numbers of qubits to be entangled simultaneously between nearest neighbors and next-nearest neighbors. Certain implementations include electrical and optical access channels for addressing, control, detection, and readout as are needed to engineer scalable quantum processors. Arrays of qubits that are fully connected provide more efficient, flexible choices for executing quantum algorithms in hardware than designs in which entangled gate operations are limited to specific pairs, due to type of qubit employed or their layout. This improved efficiency and flexibility grows rapidly with the number of qubits in an array. Adding a capability to perform gate operations involving more than two qubits at a time can significantly accelerate the efficiency gains over designs limited to one- and two-qubit gates, tens of which can be replaced with one four-qubit gate. Certain implementations described herein use multiple qubit arrays in (e.g., multiple directly connected planar arrays and/or

linear arrays) to advantageously avoid problems of one- and two-dimensional geometry configurations (e.g., limits on connectivity; crowding of electrodes needed to control each qubit in a gate, which can greatly extend gate spacing). In certain implementations, multi-dimensional cells of qubits are formed that resemble crystals, such as pyrochlores. Inverting qubits and cells (e.g., in alternating rows) can enable closer cell tiling and space for optical access, controls and readout. Utilizing many qubits to participate per gate can also reduce requirements of circuit depth, error correction and interference mitigation. Interchangeable component cells can enable quantum FPGA (QFPGA) and ASIC (QASIC) chips.

(23) Certain implementations of the QC system described herein comprise multi-layer configurations comprising multiple fully-connected qubits arranged as arrays of three-dimensional (3-D) lattice structures (e.g., cells) with simultaneous multi-qubit gate operations enabled by qubits arrayed in geometric layouts. For example, multiple planar or linear qubit arrays in layers (e.g., rows and columns; lattice; chains) can be substantially parallel to one another and can form arrays of 3-D cells that can be analogized to or referred to as crystal structures. In certain implementations, the qubits can be suspended (e.g., trapped) equivalently above and below (or over and under; left and right of; etc.) multiple co-aligned qubit containment zones (e.g., facing parallel ion trap arrays) to enable optimal coherent connectivity (e.g., entanglement) directly between nearest neighbor qubits, next-nearest neighbor qubits, etc. across multiple array substantially planar regions (e.g., layers; levels; planes) without requiring photonic or other interconnects entailing lossy conversions of in situ processing qubits to other species or data bits or significant time delays. Certain such implementations utilize geometrically symmetric cellular structures that provide a capability to perform gate operations involving more than two qubits at a time, which can significantly accelerate the efficiency gains over designs limited to one- and two-qubit gates, tens of which can be replaced with one four-qubit gate. Certain implementations described herein use qubit arrays in multiple directly connected substantially planar regions (e.g., layers; levels; planes) to advantageously avoid problems of one- and two-dimensional geometry configurations (e.g., limits on connectivity; crowding of electrodes needed to control each qubit in a gate, which can greatly extend gate spacing). In certain implementations, multi-dimensional cells of qubits are formed that resemble crystals, such as pyrochlores. Inverting qubits and cells (e.g., in alternating rows) can enable closer cell tiling and space for optical access, controls and readout. Utilizing many qubits to participate per gate can also reduce minimize requirements of circuit depth, error correction and interference mitigation. Interchangeable component cells can enable quantum FPGA (QFPGA) and ASIC (QASIC) chips.

(24) While various implementations are described herein according to the physics of trapped ion qubit approaches, other qubit approaches (e.g., superconducting qubits) can also be used in accordance with certain implementations described herein without loss of generality.

(25) Certain implementations of the QC system described herein comprises a plurality of multiple-qubit three dimensional (3-D) gate cells, each cell comprising at least three qubits that can be fully connected simultaneously across three dimensions, and a plurality of multiple-qubit cells configured for gate operations of two or more of the multiple-qubit gates. The QC system of certain such implementations can comprise multiple co-aligned qubit containment zones, such as facing parallel ion trap arrays, that enable optimal coherent connectivity or entanglement directly between nearest neighbor qubits, next-nearest neighbor qubits, etc. across multiple array layers, levels or planes without requiring photonic or other interconnects. The multiple-qubit cells can be configured using geometric symmetry to enable multiple-qubit gates to be affected natively, in one gate operation, without reliance on concatenations of multiple one- and two-qubit gates.

Leveraging the symmetry of equilateral coupling distances between multiple qubits in a cell enables more than two entangled qubits at a time to perform gate operations that would otherwise require many more qubit gate operations comprising only one- and two-qubit gates. The multiple-qubit cells can comprise or include asymmetric 3-D structures with complementary bases and caps

arranged in alternating orientations up and down, left and right, or other opposing-face orientations. This alternating arrangement of asymmetric 3-D cells can enable interleaving of non-identical neighboring cell bases and caps including their extended or overlapping electrode regions to yield optimal tiling and spacing of cells of given size or area. Lattices or arrays of the multiple alternating orientations of asymmetric cell structures can reduce problems of one- and two-dimensional geometry configurations such as: crowding of electrodes needed to control each qubit in a gate, which detrimentally increases gate spacing; limited optical accesses; complicated stray light management; limited electrical connectivity; and others. Qubits and cells can be inverted in alternating rows in ways that enable closer cell tiling and open intercell channel spaces for optical access, controls and readout. The symmetric or equilateral coupling geometries of the multiple qubits per cell can enable more complex quantum gates to be performed in a single gate operation and can additionally reduce requirements of circuit depth, error correction and interference mitigation. The interchangeable component cells can enable quantum FPGA (QFPGA) and ASIC (QASIC) chips and can be highly reconfigurable.

(26) Certain implementations of the QC system described herein advantageously provide a three-dimensional (3-D) layout of qubits and/or qubit gates that facilitate many more qubits and/or qubit gates being used for computations than are provided using one-dimensional (1-D) or two-dimensional (2-D) layouts (see, e.g., J. I. Cirac and P. Zoller, "A scalable quantum computer with ions in an array of microtraps," *Nature*, Vol. 404, p. 579 (2000); J. Chiaverini et al., *Quant. Inf. Comp.* Vol. 5, 419 (2005)). For example, certain implementations described herein provide a 3-D layout of qubit gates, each comprising multiple ions (e.g., four or more simultaneously entangled ions), while providing sufficient spacing to facilitate electrical connections and optical pathways for addressing, manipulation, control, readout, and potential sideband cooling of each qubit, and providing line of sight access angles.

(27) When a particular arrangement or set of qubits allows for any qubit to be quantum mechanically entangled directly with any other qubit in the set, the qubits can be described as being "fully connected." Even a small number of qubits comprising ions that are fully connected in a one-dimensional (1-D) linear ion trap can demonstrate measurably greater potential processing power than can the same number of qubits that are only pair-wise connected (see, e.g., N. M. Linke et al., "Experimental comparison of two quantum computing architectures", *PNAS*, Vol. 114, no. 13 (2017)).

(28) Quantum computing (QC) designs demonstrated over the past two decades indicate that the parameters which most affect how quickly a quantum computer can outperform its classical computer counterpart are not based simply on how many qubits are wired together in some fashion. This is exemplified by the greater degree of interest in circuit-model QC hardware, which often has less than one-hundredth of the number of qubits claimed by the leading quantum annealing approach that does not perform a single gate operation. Demonstrated performance of such systems has come down to qubit fidelities (e.g., how precisely the system can perform gate operations), how the qubits are interconnected, and how much overhead is used to allow the qubits to work together to compute solutions to hard problems.

(29) One-qubit gates simply entail flipping a qubit by itself from "0" to "1" or to a special quantum superposition of "0" and "1". Two-qubit gates connect two qubits using superposition combined with quantum entanglement such that anything done to one of the qubits affects the other. In such a two-qubit gate, a target qubit may start out in state "0" or state "1", and can be in any superposition of "0" and "1" (e.g., halfway between "0" and "1"). For example, the function of a quantum controlled-NOT (CNOT) gate is to flip the target qubit if the control qubit is in state "1"; otherwise it does nothing. One- or two-qubit gates can be implemented directly in many different quantum gate-based architectures. For more complex gate operations, implementations that can entangle more than two qubits at once can have a significant impact on the total number of qubits and steps performed to effect the operation and the algorithms that incorporate them (see, e.g., C. Figgatt et

al., “Parallel entangling operations on a universal ion-trap quantum computer,” *Nature*, Vol. 571 (2019); Y. Lu et al., “Global entangling gates on arbitrary qubits,” *Nature*, Vol. 571 (2019)). Measurable reductions in the numbers of qubits and steps used up front can, in some instances, lead to dramatic reductions in the overhead for achieving successful outcomes. One example would be a prototype demonstration that could give solutions to otherwise intractable problems without extensive error correction and with fewer ancillas, even part of the time.

(30) Certain implementations described herein use multiple fully connected, high-fidelity qubits. The advantages of such certain implementations (e.g., how much more efficient a particular quantum gate operation can be, as opposed to using combinations of one- and two-qubit gates) can be illustrated by considering an example quantum triply-controlled-NOT (C.sup.3NOT) gate comprising four fully connected, high-fidelity qubits. The C.sup.3NOT gate is also called a super-Toffoli gate. In this example C.sup.3NOT gate, three control qubits must all be in a specified state (e.g., “1,1,1”) in order to flip a fourth target qubit from “1” to 0”. When combined with one or more single-qubit gate operations, such multi-qubit quantum gates can be used to complete a universal set for quantum computing. Multiply-controlled NOT gates are described in reference sources generally as comprising extended series of one- and two-qubit gate operations (see, e.g., M. A. Nielsen and I. L. Chuang, “Quantum Computing and Quantum Information,” 1st ed. (Cambridge Univ. Press, 2000)). The extent to which these one- and two-qubit gate series increase even more in physical implementations depends on type of qubits used and on how many qubits can be fully connected and entangled with one another. However, a C.sup.3NOT gate implemented using four fully-connected, multiply-entangled ions at the same time, in an appropriate physical layout, can be configured with a small fraction of the number of the quantum gate operations used in a C.sup.3NOT gate implemented only with one- and two-qubit gates. This can be done by starting with an extension of methods described for implementing the simpler C.sup.2NOT Toffoli gate (see, e.g., J. I. Cirac and P. Zoller, “Quantum Computations with Cold Trapped Ions,” *Phys. Rev. Lett.* Vol. 74 (20) (1995)) and later demonstrated (see, e.g., T. Monz et al., “Realization of the Quantum Toffoli gate with Trapped Ions,” *Phys. Rev. Lett.* Vol. 102, 040501 (2009)). The three-qubit C.sup.2NOT implementation already exhibited a significant reduction in number of contributing gates and time required to complete the full gate operation, while yielding an improvement in net fidelity over the concatenation of one- and two-qubit gates, even if they were of much higher individual fidelities, due to aggregated gate errors. This three-qubit gate can be realized in a linear trap without a strong requirement for geometric symmetry. In contrast, certain implementations described herein provide C.sup.nNOT gates by exploiting the full 3-D symmetries of the designs described herein. In this way, the improved efficiency example referenced above can be greatly multiplied according to the number of controls in each C.sup.nNOT gate through concomitant reductions in quantum gates needed to implement them. Other multiply-controlled gate operations, including phase rotations, can exhibit similar improvements in efficiency using a physical configuration that involves more than two entangled qubits simultaneously. These improvements up front can greatly reduce error correction.

(31) Even the highest quality qubits exhibit noticeable error rates, which can be small on a per-qubit basis but get multiplied by the number of gates that are used to run an algorithm. When the aggregate error rate reaches a threshold where error correction is required to perform even a small set of quantum operations with reasonable chance of giving a reliable result, the efficiency of the architecture immediately drops in proportion to the amount of overhead used for the error correction.

(32) For a small scale quantum computer having a few hundred relatively high quality qubits intended to perform logic operations, the overhead of error-correction qubits plus ancillas can represent an increase in the number of qubits of one order of magnitude or roughly a factor of ten, with a proportionate decrease in efficiency. For larger scale systems, the overhead can increase further to multiple orders of magnitude. However, in certain implementations described herein, a

quantum computer that benefits from aggregate efficiencies of fully-connected, high-quality qubits and employs multi-qubit gate operations (e.g., performed natively by exploiting multi-dimensional geometry) can use significantly fewer steps and significantly fewer total numbers of qubits. As used herein, the term “native” gate operations indicates that more than two qubits can participate at the same time, by virtue of a geometric layout. Certain native multi-qubit gate implementations described herein can advantageously perform algorithms without using extensive error correction overhead. In addition, significant improvements in overall design efficiency, due to reduced overhead, can be achieved, using multiple orders of magnitude fewer quantum resources, both to perform basic quantum computing algorithms or subroutines and to show practical utility with increased speed as compared to classical computing systems.

(33) To date, most QC systems using trapped ions employ one-dimensional (e.g., linear) traps, which can then be interconnected electrically or photonically (see, e.g., U.S. Pat. No. 9,858,531; Debnath et al., “Demonstration of a small programmable quantum computer with atomic qubits,” *Nature*, Vol. 536, p. 63 (2016)). Such 1-D traps enable a linear chain of qubits to be fully connected within a common potential well or trapping zone. The extent of full connectivity is limited by how many qubits can be chained together before the coupling strength between qubits at or near opposite endpoints of the linear chain is too weak to be usable for reliable multi-qubit gate operations, so it can be desirable to create interconnects between multiple linear traps of limited lengths. Optical interconnects, for example, can be employed by transferring a qubit state from an ion to a photon, then sending the photon to another linear trap where the quantum state is transferred to another ion. One type of protocol that is commonly used for such a process is termed “quantum teleportation.” Such interconnections impart time delays and potential inefficiencies in the conversions (e.g., from a trapped ion qubit to a photon, and to a second trapped ion). Certain implementations described herein advantageously provide an alternate configuration to optimize more direct qubit-to-qubit interactions simultaneously than can be done efficiently using linear or 2-D elements with optical interconnects. When scaling up to larger numbers of qubits, certain such implementations can advantageously reduce or stave off the number of optical interconnections between nodes with their associated penalties (e.g., time delays; ion-photon conversion losses).

(34) Rectangular two-dimensional (2-D) grid configurations have been previously adopted for some trapped ion approaches, as well as for superconducting qubit (SCQ) schemes. However, the interactions between qubits have been limited to one- and two-qubit operations that occur within the trapped ion grid lanes (e.g., by shuttling qubits in and out of lanes through intersections). Such approaches rely on significant redundancy to add the degree of fault tolerance for raising the probability of success in running an algorithm to usable levels. For example, some approaches use global addressing of ensembles of qubits, which are shuttled in and out of aligned intersections in a grid in order to effect a single one- or two-qubit operation redundantly among the many qubits, and then average to reduce errors. The overhead in such an approach, in terms of numbers of redundant qubits for effecting a single logic operation with sufficient fidelity, grows rapidly with the scale of the logic operations to be performed by the quantum computer. Conversely, in certain implementations described herein, entanglement between more than two qubits is enabled by having the qubits arranged in two or more dimensions, to be involved simultaneously and to effect multi-qubit gate operations directly or natively.

(35) To distinguish certain implementations described herein from other approaches in which descriptive terms and visual layouts may appear similar, it is noted that the overall layout of 2-D periodic crystal structures, such as triangular lattice Penning traps (e.g., a surface of periodic electropotential wells into which ions can be placed to form an extended 2-D crystal or triangular lattice; useful for studying the physics of many-body interactions but not for implementing gate operations between multiple qubits; and hexagonal Kitaev models can resemble, but are different from, portions (e.g., single layers) of certain multi-layer implementations described herein (see, e.g., A. Kitaev, *Ann. Phys.* Vol. 321, 2 (2006); R. Schmied et al. *New J. Phys.* 13 115011 (2011))

(“Schmied 2011”). However, such 2-D periodic crystal structures are significantly different in design complexity and purpose to certain implementations described herein. For example, such crystal lattice structures have been designed only for simulations of quantum systems. Such structures are generally not intended to perform gate operations, but can be used to form energy topologies that mimic those of the quantum system to be modeled (e.g., to find the slowest electron energy configuration of a given molecule). In particular, a quantum simulator having a 2-D hexagonal lattice of ions (e.g., following the Kitaev model) generally can use fewer electrode structures than the number of electrode structures of a “full-up” quantum computer capable of quantum gate operations. Therefore, the shapes of the electrode structures of quantum simulators are less affected by overall design constraints than are the shapes of electrode structures for scalable gate-based quantum computing.

(36) Nevertheless, algorithms can be used to help design (e.g., optimize) the electrode structures for trapping and holding individual ions in a periodic lattice (e.g., for individual trapping zones in a larger trapped ion architecture) for a gate-model quantum computer (see, e.g., R. Schmied, et al. Phys Rev. Lett. 2009 (“Schmied 2009”). One general guideline for electrode structure design obtainable from Schmied 2009 is that, given M traps (e.g., microtraps) per unit cell, the number of surface patch electrodes generally is at least 8M for full control and for effective gate operations.

(37) In addition, crowding of the surface electrodes for controlling each ion of a 2-D layer of trapped ions for gate operations can arise. Such crowding can be due to the areas of the eight or more surface electrodes that provide full control of an ion in its electropotential well, limiting how closely ion trapping zones can be placed together and still allow for strong coupling for effective gate interactions. The coupling strength is highly dependent on the inter-ion distance (d), with the coupling strength or the exchange frequency Ω_{ex} rolling off as $1/d^3$ as shown in the equation:

$$(38) \quad \Omega_{\text{ex}} = \frac{q_1 q_2}{4 \sqrt{m_1 m_2} d^3}$$

(39) where Ω_{ex} is the exchange frequency or coupling strength, and for the most general case in which more than one ion species may be used, q_1 is the charge of an ion in a first electropotential well, identified here as potential well “1”, q_2 is the charge of an ion in a second potential well identified here as potential well “2”, m_1 and m_2 are the masses of the ions in potential wells 1 and 2, respectively, ω_1 and ω_2 are the frequencies of potential wells 1 and 2, respectively, and d is the distance between the ions (see, e.g., D. J. Wineland et al., J. Res. Natl. Inst. Stand. Technol. Vol. 103, 259 (1998)).

(40) Certain implementations described herein advantageously facilitate solutions to other hardware challenges, which can grow rapidly and appear daunting or infeasible when designing gate-model QC structures that are scaled up from 2-D trapped ion lattices. For example, certain implementations described herein integrate optical elements (e.g., lasers; optical ports; fibers; detectors) into the QC structure for addressing, manipulation, readout, and potential sideband cooling of each qubit, and provide line of sight access angles.

(41) Certain implementations described herein advantageously provide scalable hardware configurations on which it is possible to directly “write” and run complex quantum algorithms by enabling simultaneous entanglement between optimal numbers of neighboring qubits. In certain implementations, a multidimensional quantum gate implementation, analogous to conventional firmware such as a field programmable gate array (FPGA), can be written directly in the form of multi-qubit gates and reprogrammed flexibly.

(42) Certain implementations described herein advantageously enable multiply controlled quantum gate operations to be run natively by exploiting multi-dimensional geometry. In certain implementations, the quantum gate operations are run on a quantum firmware platform in the least number of steps (e.g., without resorting to concatenations of one- and two-qubit gate operations to effect a multiply controlled NOT operation).

- (43) Certain implementations described herein advantageously provide a realizable engineering configuration that enables the quantum firmware platform to be scaled up as needed by integrating electrical and optical channels for full control and readout of each qubit in a circuit-model architecture to enable universal quantum computing.
- (44) Certain implementations described herein advantageously provide a multi-layer quantum computing structure configured to enable optimal numbers of qubits to be entangled simultaneously between nearest neighbors, next-nearest neighbors, and potentially beyond. Certain such implementations include electrical and optical access channels for addressing, control, and readout of qubits in scalable quantum processors. For example, arrays of qubits that are fully connected advantageously provide more efficient, flexible choices for executing quantum algorithms in hardware than do other designs in which entangled gate operations are limited to specific pairs (e.g., due to the type of qubit employed or their layout). This improved efficiency and flexibility can grow rapidly with the number of qubits in an array.
- (45) Certain implementations described herein are advantageously able to perform gate operations involving more than two qubits at a time, thereby providing significant improvements of efficiency over previous designs that are limited to one- and two-qubit gates (e.g., by replacing tens of such gates with one four-qubit gate). Certain implementations described herein advantageously overcome connectivity limitations found in one- and two-dimensional geometries using trapped ions. For example, arraying qubits in multiple qubit arrays (e.g., multiple planar and/or linear qubit arrays) with direct connectivity (e.g., entanglement) between the qubit arrays can solve the problem of significant time delays and inefficiencies of converting from ion qubits to photonic qubits and back again to continue scaling up from a few tens of ions in a 1-D chain. In addition, array qubits in multiple planes can solve issues arising from crowding of electrodes for controlling each qubit in a gate, which otherwise greatly extends gate spacings. For another example, selectively inverting electropotential wells between facing surface planes can enable a maximum number of neighboring qubits to participate in a gate operation.
- (46) Certain implementations described herein advantageously utilize a first set of ions trapped above a first surface and a second set of ions trapped below a second surface, the second surface facing the first surface and at least some ions of the first set of ions entangled with at least some ions of the second set of ions. By integrating and interleaving the first and second sets of trapped ions and by adjusting the trap height of a central ion of the qubit gate relative to ions at vertices of the qubit gates, certain implementations advantageously provide multi-dimensional entangling geometries that resemble complex 3-D crystalline structures (e.g., a pyrochlore). In addition, the space between the first and second surfaces of certain implementations advantageously provides optical access from the sides for addressing the qubits globally or locally, as well as optical access for readout by detectors. The multiple-ion qubit gates (e.g., cells) can be constructed asymmetrically such that a cap of each cell (e.g., either up or down) provides additional space for integrating optics and electronics to be used to initialize, manipulate, and read out qubits individually or as ensembles. For example, rows of these multiple-ion qubit gates (e.g., cells) can be interleaved, with alternating “up” and “down” cell orientations to form channels that provide additional multi-angle optical accesses and electronic control lines between rows of cells. Since gravity is not the dominant force on trapped ions, the full configuration can be oriented at any angle (e.g. tilted 90 degrees, where “up” and “down” are replaced “left” and “right” etc.). For other types of qubits, this general directional insensitivity of trapped ions may not apply to the same degree, and other types of qubits may confine the choices of orientation.

Example Implementations

- (47) Certain implementations described herein utilize multi-dimensional cells of qubits, which can resemble 3-D crystal structures (e.g., pyrochlores). In certain implementations, inverting the cells in alternating rows enables closer cell tiling and space for optical access, controls, and readout. Certain implementations utilize many qubits per gate, advantageously reducing (e.g., minimizing)

circuit depth, error correction, and interference mitigation. Certain implementations utilize interchangeable component cells which can advantageously enable quantum FPGA (QFPGA) and quantum ASIC (QASIC) chips.

(48) While the physical configurations of certain implementations are described herein as using high fidelity trapped ion qubits (e.g., with low error rates), any type of qubit (e.g., naturally occurring; artificially formed) that can be entangled in multiple dimensions simultaneously with multiple other qubits can be used in accordance with certain implementations described herein. Examples of qubits compatible with certain implementations described herein include but are not limited to: subatomic particles; neutral atoms; ions; neutral molecules; charged molecules; Bose-Einstein condensates; electrons; electron holes; excitons; magnetic qubits; nitrogen-vacancy centers in diamond; phonons; photons; quantum dots; Rydberg atoms; spins in silicon; and possibly superconducting qubits. In certain implementations, the qubits are suitable to effect gate operations directly (e.g., natively), between more than two qubits in the specified configuration. For example, the physical architecture of certain implementations can advantageously provide complex gate operations directly, such as a multiply-controlled NOT or phase rotation, without resorting to serial concatenations of one- and two-qubit gates.

(49) The trapped ion qubits utilized in certain implementations described herein, illustrate the nature of quantum interactions to be optimized. Germane figures of merit that trapped ions exhibit include but are not limited to: (i) the fact that they are identical within a given species and therefore extensive calibration or tuning can advantageously be avoided, (ii) the ability to form qubits that have very long-lived stability, and (iii) continued, demonstrated high fidelity gate operations as compared to competing qubit technologies. In certain implementations described herein, simultaneous multi-qubit gate operations can be enabled by ions arrayed in 3-D geometric layouts of multiple identical, fully-connected qubits.

(50) FIGS. 1A-1C and 2A-2D schematically illustrate various aspects of example multiple-qubit gates (e.g., cells) in accordance with certain implementations described herein. The qubit gates are formed by interspersing electropotential wells both above and below parallel surface planes and using the electropotential wells to trap ions that are entangled with other trapped ions. Examples of ions compatible with certain implementations described herein include but are not limited to: Ba.sup.+; Be.sup.+; Cd.sup.+; Ca.sup.+; Mg.sup.+; Hg.sup.+; Sr.sup.+; Yb.sup.+. Vertical orientation is not required, so the terms “top” and “bottom” are not used.

(51) FIG. 1A schematically illustrates a side-angle view and a top view of an example single-ion portion **10** of an example four-ion qubit gate **100** in accordance with certain implementations described herein. The single-ion portion **10** comprises a substantially planar substrate region **12**, one or more electrical traces **14**, an electrode region **16** comprising one or more electrodes (not shown), an electropotential well **17**, and a single ion **18**. In certain implementations, the substrate region **12** comprises a portion of an electrical insulator and/or semiconductor (e.g., silicon oxide; silicon) chip, and at least some of the electrical traces **14** are in electrical communication with the electrodes of the electrode region **16**. At least some of the other electrical traces **14** can be in electrical communication with the electrodes of the electrode regions of portions of other neighboring qubits. For example, the electrical traces **14** and the electrodes within the electrode region **16** can comprise electrically conductive material (e.g., aluminum; copper; gold) deposited onto a surface of the substrate region **12**, and can comprise at least one hermetic coating configured to hermetically seal the electrically conductive material from contaminants and/or corrosion. The electrodes of the electrode region **16** are configured to generate the electropotential well **17** which is configured to contain (e.g., suspend; trap) the single ion **18** at a position spaced away from the planar substrate region **12** (e.g., in a direction substantially perpendicular to the substrate region **12**).

(52) FIG. 1B schematically illustrates a side-angle view and a top view of an example three-ion portion **30** of the example four-ion qubit gate **100** in accordance with certain implementations

described herein. The three-ion portion **30** comprises a substantially planar substrate region **32**, one or more electrical traces (not shown), an electrode region **36** comprising multiple electrodes (not shown), three electropotential well **37a-c**, and three ions **38a-c**. In certain implementations, the substrate region **32** comprises a portion of an electrical insulator and/or semiconductor (e.g., silicon oxide; silicon) chip, and at least some of the electrical traces are in electrical communication with the electrodes of the electrode region **36**. At least some of the other electrical traces can be in electrical communication with the electrodes of the electrode regions of other portions of neighboring qubits. For example, the electrical traces and the electrodes within the electrode region **36** can comprise electrically conductive material (e.g., aluminum; copper; gold) deposited onto a surface of the substrate region **32**, and can comprise at least one hermetic coating configured to hermetically seal the electrically conductive material from contaminants and/or corrosion. In certain implementations, electrical traces **14** that are in electrical communication with electrodes within region **36** or other electrode regions can be in substrate layers (not shown) beneath the surface (e.g., sub-surface) and can run substantially consistently with other electrical traces **14** on the surface. The electrodes of the electrode region **36** are configured to generate the three electropotential wells **37a-c**, each of which is configured to contain (e.g., suspend; trap) a corresponding one of the three ions **38a-c** at a position spaced away from the planar substrate region **32** (e.g., in a direction substantially perpendicular to the substrate region **32**). In certain implementations, the three ions **38a-c** form an equilateral triangle (e.g., spaced from one another by a distance in a range of 30 microns to 40 microns), with the triangle substantially parallel to the substrate region **32**. The three ions **38a-c** of the triangle are an example of three qubits arranged in a substantially planar region and configured to interact with one another in accordance with certain implementations described herein.

(53) In certain implementations, as shown in FIGS. **1A-1B**, the substrate region **12** of the single-ion portion **10** and the substrate region **32** of the three-ion portion **30** (e.g., the portions of the respective chips that generally correspond to the four-ion qubit gate **100**) have a substantially hexagonal shape, while in certain other implementations, the substrate regions **12**, **32** have other shapes (e.g., rectangular; square; triangular; circular; oval; geometric; non-geometric; symmetric; non-symmetric).

(54) The hashed regions of FIGS. **1A** and **1B** corresponding to the electrode regions **16**, **36** (e.g., electrode patch zones) represent general “write” zones that are positioned and shaped to accommodate the multiple individual electrodes within each zone for generating the electropotential wells **17**, **37a-c** for confining the corresponding ions **18**, **38a-c**. The positioning and shaping of the various electrodes for the particular configurable gate implementation can be designed using algorithms (e.g., as provided by Schmied 2009). In certain implementations, the electrode regions **16**, **36** are configured to trap, fully control, and perform gate operations using the corresponding ions **18**, **38a-c**. For example, the electrode region **36** of FIG. **1B** can include eight or more electrodes per ion trap zone. In certain implementations, the electrodes and the electrode regions **16**, **36** are based on previously developed electrodes and electrode regions for 2-D layouts for trapped ions (see, e.g., C. W. Hogle et al., “Characterization of Microfabricated Surface Ion Traps,” Sandia National Lab., SAND2017-6113C (2017)).

(55) FIG. **1C** schematically illustrates a side-angle view and a top view of the example four-ion qubit gate **100** comprising the single-ion portion **10** of FIG. **1A** (e.g., as a “cap” of the four-ion qubit gate **100**) and the three-ion portion **30** of FIG. **1B** (e.g., as a “base” of the four-ion qubit gate **100**), with the ions **18**, **38a-c** configured to be fully-connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously or in any subset combination), in accordance with certain implementations described herein. The example four-ion qubit gate **100** of FIG. **1A** has a substantially hexagonal shape, while in certain other implementations, the qubit gate **100** has other shapes (e.g., rectangular; square; triangular; circular; oval; geometric; non-geometric; symmetric; non-symmetric). In certain implementations, the qubit gate **100** has a width W (e.g., in a range of

less than or equal to 0.2 mm). While the right-side of FIG. 1C shows at least some of the electrical traces **14** on the surface of the portion **30**, in certain implementations, at least some of the electrical traces **14** are in substrate layers (not shown) beneath the surface (e.g., sub-surface) and can run substantially consistently with other electrical traces **14** on the surface. In certain implementations, the substrate region **12** is substantially parallel to the substrate region **32** and the substrate region **12** is spaced from the substrate region **32** by a distance S (e.g., in a range less than or equal to 0.2 mm). In certain implementations, the single ion **18** is spaced from each of the three ions **38a-c** (e.g., by a distance in a range of 30 microns to 45 microns) and is positioned above the center of the triangle formed by the three ions **38a-c**. Each of the ions **18**, **38a-c** is entangled with each of the other ions **18**, **38a-c**, as denoted by the dashed lines in FIG. 1C. In certain implementations, the example four-ion qubit gate **100** has a width W (e.g., in a range of less than or equal to 0.2 mm). The three ions **38a-c** are an example of three qubits arranged in a first substantially planar region (e.g., the distances of the three ions **38a-c** from the substrate region **32** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another) and the single ion **18** is an example of a qubit arranged in a second substantially planar region substantially parallel to the first substantially planar region. The qubit of the second substantially planar region is configured to interact with the three qubits of the first substantially planar region which are configured to interact with one another, in accordance with certain implementations described herein.

(56) In certain implementations, the example four-ion qubit gate **100** of FIG. 1C is used as a “native” C.sup.3NOT gate (e.g., a triply-controlled NOT gate) and/or as “native” C.sup.3 ϕ gate (e.g., a triply-controlled phase gate). The example four-ion qubit gate **100** of certain implementations can effect a C.sup.3NOT/C.sup.3 ϕ gate with significantly fewer gate operations than would be used by one- or two-qubit gates alone. In certain implementations, the net fidelity of the native C.sup.3NOT/C.sup.3 ϕ gate provided by the example four-ion qubit gate **100** is significantly greater than that of a C.sup.3NOT/C.sup.3 ϕ gate comprising many two-qubit gates that may have much higher individual gate fidelities, since the four-ion qubit gate **100** does not aggregate the errors of many successive operations to achieve its result. In certain such implementations, the C.sup.3NOT/C.sup.3 ϕ gate provided by the example four-ion qubit gate **100** uses a fraction of the steps of a C.sup.3NOT/C.sup.3 ϕ gate comprising many two-qubit gates, so the C.sup.3NOT/C.sup.3 ϕ gate provided by the example four-ion qubit gate **100** is faster and less error-prone (e.g., thereby utilizing significantly less error correction at the outset), as can be seen in a comparison of the probabilities of successful gate operation using both structures and fidelity estimates.

(57) FIG. 2A schematically illustrates a side-angle view of an example seven-ion qubit gate **200** in accordance with certain implementations described herein. In certain implementations, the example seven-ion qubit gate **200** of FIG. 2A is configured to be used as a native C.sup.6NOT/C.sup.6 ϕ gate. The example seven-ion qubit gate **200** of FIG. 2A comprises the single-ion portion **10** of FIG. 1A (e.g., as a “cap” of the seven-ion qubit gate **200**) and a six-ion portion (e.g., as a “base” of the seven-ion qubit gate **200**). The six-ion portion **50** comprises a planar substrate region **52**, one or more electrical traces (not shown), six electrode regions **56a-f**, six electropotential wells **57a-f**, and six ions **58a-f**. The electrodes of the electrode regions **56a-f** are configured to generate the six electropotential wells **57a-f**, each of which is configured to contain (e.g., suspend; trap) a corresponding one of the six ions **58a-f** at a position spaced away from the planar substrate region **52** (e.g., in a direction substantially perpendicular to the substrate region **52**). As schematically illustrated by FIG. 2A, the example seven-ion qubit gate **200** can comprise an additional electrode **59** (e.g., a cover electrode) (see, e.g., C. E. Pearson et al., Phys. Rev. A Vol. 73, 032307 (2006)) positioned below the single ion **18** of the single-ion portion **10** and configured to aid tuning of the distance of the single ion **18** relative to the six-ion portion **50**. In certain implementations, the six ions **58a-f** form an equilateral hexagon (e.g., spaced from one another by a distance in a range of 35 microns to 70 microns), with the hexagon substantially parallel to the substrate region **52**. The

spacing of the hexagons from one another can be set based on various parameters, including but not limited to: multiple tuning parameters, ion species, crystal lattice angles formed. In certain implementations, the distance of each qubit in the hexagon from the nearest substrate can have variability (e.g., at a nominal distance of 40 microns \pm 5 microns), as a result of 3-D angles in the crystal lattice. The seven ions **18**, **58a-f** are configured to be fully connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously, or in any subset combination), as schematically illustrated by the dotted lines which denote entanglements among the seven ions **18**, **58a-f**. As schematically illustrated in FIG. 2A, in certain implementations, portions of the electrode regions **56a-f** of the six-ion portion **50** extend onto the substrate regions of the bases of neighboring qubits and portions of the electrode regions of neighboring portions extend onto the substrate region **12** of the single-ion portion **10**. The six ions **58a-f** are an example of six qubits arranged substantially in a first substantially planar region (e.g., the distances of the six ions **58a-f** from the substrate portion **52** can be within \pm 5 microns, within \pm 2 microns, and/or within \pm 1 micron of one another) and the single ion **18** is an example of a qubit arranged in a second substantially planar region substantially parallel to the first substantially planar region. The qubit of the second substantially planar region is configured to interact with the six qubits of the first substantially planar region which are configured to interact with one another, in accordance with certain implementations described herein.

(58) In certain implementations, the single ion **18** is contained (e.g., suspended; trapped) in a first electropotential well **17**, the single ion **18** at a first distance (e.g., 40 microns) from the electrode region **16**. In certain other implementations, the single ion **18** is contained in a second electropotential well, the single ion **18** at a second distance from the substrate region **52**, the second distance approximately twice the first distance (e.g., 80 microns). For example, the second electropotential well can be formed naturally (see, e.g., M. Mielenz et al., “Arrays of individually controlled ions suitable for two-dimensional quantum simulations,” Nature Communications, 7:11839 (2016)). In certain implementations, the first electropotential well **17** and the second electropotential well coincide or overlap with one another such that the single ion **18** is contained in both the first and second electropotential wells concurrently, while in certain other implementations, the first and second electropotential wells are separate from one another.

(59) FIG. 2B schematically illustrates a side-angle view and a top view of an example eight-ion qubit gate **300** in accordance with certain implementations described herein. In certain implementations, the example eight-ion qubit gate **300** of FIG. 2B is configured to be used up to a C.sup.7NOT/C.sup.7 ϕ gate. The example eight-ion qubit gate **300** of FIG. 2B comprises the single-ion portion **10** of FIG. 1A (e.g., as a “cap” of the eight-ion qubit gate **300**) and a seven-ion portion (e.g., as a “base” of the eight-ion qubit gate **300**). The seven-ion portion **70** comprises a planar substrate region **72**, one or more electrical traces (not shown), seven electrode regions **76a-g**, seven electropotential wells **77a-g**, and seven ions **78a-g**. The electrodes of the electrode regions **76a-g** are configured to generate the seven electropotential wells **77a-g**, each of which is configured to contain (e.g., suspend; trap) a corresponding one of the seven ions **78a-g** at a position spaced away from the planar substrate region **72** (e.g., in a direction substantially perpendicular to the substrate region **72**). The example eight-ion qubit **300** of FIG. 2B is similar to the seven-ion qubit gate **200** of FIG. 2A, with the addition of the eighth electrode region **76g**, eighth electropotential well **77g**, and eighth ion **78g** (e.g., positioned in a range of 30 to 60 microns above the electrode region **76g**). The distance of the eighth ion **78g** from the substrate region **72** can be based on various factors, including but not limited to whether the seven-ion portion **70** is combined with a single-ion portion a three-ion portion **30**, or another multiple-ion portion as described herein. The eight ions **18**, **78a-g** are configured to be fully connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously, or in any subset combination) (dotted lines denoting entanglements among the eight ions **18**, **78a-g** are omitted from FIG. 2B for the sake of clarity). The six ions **78a-f** are an example of six qubits arranged substantially in a first substantially planar region (e.g., the distances

of the six ions **78a-f** from the substrate portion **72** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another), the seventh ion **78g** is an example of a qubit arranged in a second substantially planar region substantially parallel to the first substantially planar region, and the single ion **18** is an example of a qubit arranged in a third substantially planar region substantially parallel to the first substantially planar region. The qubit of the second substantially planar region and the qubit of the third substantially planar region are configured to interact with one another and with the six qubits of the first substantially planar region which are configured to interact with one another, in accordance with certain implementations described herein.

(60) With regard to the example seven-ion qubit gate **200** of FIG. 2A and the example eight-ion qubit gate **300** of FIG. 2B, in certain implementations, each of the qubit gates **200**, **300** has a substantially hexagonal shape, while in certain other implementations, the qubit gates **200**, **300** have other shapes (e.g., rectangular; square; triangular; circular; oval; geometric; non-geometric; symmetric; non-symmetric). In certain implementations, the substrate region **52**, **72** comprises a portion of an electrical insulator and/or semiconductor (e.g., silicon oxide; silicon) chip, at least some of the electrical traces are in electrical communication with the electrodes of the electrode regions **56**, **76** and other electrical traces are in electrical communication with the electrode regions of other bases. In certain implementations, each of the electrode regions **56**, **76** comprises one or more electrodes in electrical communication with at least some of the electrical traces, and the electrical traces and the electrodes within the electrode regions **56**, **76** comprise electrically conductive material (e.g., aluminum; copper; gold) deposited onto a surface of the substrate region **52**, **72**, and can comprise at least one hermetic coating configured to hermetically seal the electrically conductive material from contaminants and/or corrosion. The electrodes of the electrode regions **56**, **76** of certain implementations are configured to at least partially extend into neighboring regions (e.g., regions of neighboring qubits) and to provide space for the electrical traces to run to the electrode region of the qubit gate **200**, **300** and/or to the neighboring qubits. In certain implementations, the seven-ion qubit gate **200** and/or the eight-ion qubit gate **300** has a width W (e.g., in a range of less than or equal to 0.2 mm), the substrate region **12** is substantially parallel to the substrate region **52**, **72**, and the substrate region **12** is spaced from the substrate region **52**, **72** by a distance S (e.g., in a range less than or equal to 0.2 mm).

(61) FIG. 2C schematically illustrates a side-angle view of an example nine-ion qubit gate **400** in accordance with certain implementations described herein. In certain implementations, the nine-ion qubit gate **400** can aid cross-chip connectivity (e.g., in a QFPGA architecture or in a QASIC architecture). In certain implementations, the example nine-ion qubit gate **400** of FIG. 2C can also be configured to be used in multiply-controlled gate operations or to employ combinations of redundant control and/or target qubits to facilitate self-error-correcting gates at desired nodes. The example nine-ion qubit gate **400** of FIG. 2C comprises the six-ion portion **50** of FIG. 2A (e.g., as a “cap” of the nine-ion qubit gate **400**) and the three-ion portion (e.g., as a “base” of the nine-ion qubit gate **400**). The nine ions **38a-c**, **58a-f** are configured to be fully connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously, or in any subset combination) (dotted lines denoting entanglements among the nine ions **38a-c**, **58a-f** are omitted from FIG. 2C for the sake of clarity). The six ions **58a-f** are an example of six qubits arranged substantially in a first substantially planar region (e.g., the distances of the six ions **58a-f** from the substrate portion **52** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another) and the three ions **38a-c** are an example of three qubits arranged in a second substantially planar region (e.g., the distances of the three ions **38a-c** from the substrate portion **32** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another) substantially parallel to the first substantially planar region. The six qubits **58a-f** of the first substantially planar region are configured to interact with one another, and the three qubits **38a-c** of the second substantially planar region are configured to interact with one another and with qubits of the first substantially planar region in accordance with certain implementations described herein. In certain

implementations, the three ions **38a-c** and/or the six ions **58a-f** are further configured to interact with ions of other qubit gates neighboring the nine-ion qubit gate **400** (e.g., intercell interactions). (62) FIG. 2D schematically illustrates a side-angle view of an example ten-ion qubit gate **450** in accordance with certain implementations described herein. In certain implementations, the ten-ion qubit gate **450** can aid cross-chip connectivity (e.g., in a QFPGA architecture or in a QASIC architecture). In certain implementations, the example ten-ion qubit gate **450** of FIG. 2D can also be configured to be used in multiply-controlled gate operations (e.g., up to a C ⁹ NOT/C.sup.9 ϕ gate) or to employ combinations of redundant control and/or target qubits to facilitate self-error-correcting gates at desired nodes. The example ten-ion qubit gate **450** of FIG. 2D comprises the seven-ion portion **70** of FIG. 2B (e.g., as a “cap” of the ten-ion qubit gate **450**) and the three-ion portion **30** (e.g., as a “base” of the ten-ion qubit gate **450**). The ten ions **38a-c**, **78a-g** are configured to be fully connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously, or in any subset combination) (dotted lines denoting entanglements among the nine ions **38a-c**, **78a-g** are omitted from FIG. 2D for the sake of clarity). The six ions **78a-f** are an example of six qubits arranged substantially in a first substantially planar region (e.g., the distances of the six ions **78a-f** from the substrate portion **72** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another), the seventh ion **78g** is an example of a qubit arranged in a second substantially planar region substantially parallel to the first substantially planar region, and the three ions **38a-c** are an example of three qubits arranged in a third substantially planar region (e.g., the distances of the three ions **38a-c** from the substrate portion **32** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another) substantially parallel to the first substantially planar region. The six qubits **78a-f** of the first substantially planar region are configured to interact with one another, the three qubits **38a-c** of the third substantially planar region are configured to interact with one another, as well as with qubits of the first substantially planar region, and the single qubit of the second substantially planar region is configured to interact with qubits of the first substantially planar region and qubits of the second substantially planar region, in accordance with certain implementations described herein. In certain implementations, the three ions **38a-c** and/or the seven ions **78a-g** are further configured to interact with ions of other qubit gates neighboring the ten-ion qubit gate **450** (e.g., intercell interactions).

(63) FIG. 2E schematically illustrates two side-angle views of an example thirteen-ion qubit gate **500** (e.g., a “pyrochlore” cell) in accordance with certain implementations described herein. In certain implementations, the example thirteen-ion qubit gate **500** of FIG. 2E is configured to be used up to a C.sup.12NOT/C.sup.12 ϕ gate. The example thirteen-ion qubit gate **500** of FIG. 2E comprises the seven-ion portion **70** of FIG. 2B (e.g., as a “cap” of the thirteen-ion qubit gate **500**), with an increase in length of the electropotential well **77g**, and concomitant distance of the ion **78g** from the electrode region **76g**, along with the six-ion portion **50** (e.g., as a “base” of the thirteen-ion gate qubit **500**). The thirteen ions **58a-f**, **78a-g** are configured to be fully connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously, or in any subset combination) (dotted lines denoting entanglements among the thirteen ions **58a-f**, **78a-g** are omitted from FIG. 2E for the sake of clarity). The six ions **58a-f** are an example of six qubits arranged substantially in a first substantially planar region **502** (e.g., the distances of the six ions **58a-f** from the substrate portion **52** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another; at a distance H.sub.1 of about 40 microns from the substrate portion **52**), the six ions **78a-f** are an example of six qubits arranged substantially in a second substantially planar region **504** (e.g., the distances of the six ions **78a-f** from the substrate portion **72** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another; at a distance H.sub.1 of about microns from the substrate portion **72**) substantially parallel to the first substantially planar region **502**, and the single ion **18** is an example of a qubit arranged in a third substantially planar region **506** substantially parallel to the first substantially planar region **502** (e.g., at a distance H.sub.2 in a range of 50 microns to 60 microns from the substrate portion **72**). The six qubits of the first

substantially planar region **502** are configured to interact with one another, the six qubits of the second substantially planar region **504** are configured to interact with one another and with the six qubits of the first substantially planar region **502**, and the qubit of the third substantially planar region **506** is configured to interact with qubits of the first substantially planar region **502** and with qubits of the second substantially planar region **504**, in accordance with certain implementations described herein. In certain implementations, the six ions **58a-f** and/or the seven ions **78a-g** are further configured to interact with ions of other qubit gates neighboring the thirteen-ion qubit gate **500** (e.g., intercell interactions).

(64) FIG. 2F schematically illustrates two side-angle views of an example fourteen-ion qubit gate **550** in accordance with certain implementations described herein. In certain implementations, the example fourteen-ion qubit gate **550** of FIG. 2F is configured to be used up to a C.sup.13NOT/C.sup.13 ϕ gate. The example fourteen-ion qubit gate **550** of FIG. 2F comprises a first seven-ion portion **70** (see, e.g., FIG. 2B) (e.g., as a “cap” of the fourteen-ion qubit gate **550**), with the ion **78g** and the electropotential well **77g** of the first seven-ion portion **70** a longer distance from the substrate portion **72** than are the ion **78g** and the electropotential well **77g** of FIG. 2B. The example fourteen-ion qubit gate **550** of FIG. 2F further comprises a second seven-ion portion (see, e.g., FIG. 2B) (e.g., as a “base” of the fourteen-ion gate qubit gate **550**), with the ion **78g** and the electropotential well **77g** of the second seven-ion portion **70** a shorter distance from the substrate portion **72** than are the ion **78g** and the electropotential well **77g** of FIG. 2B. The first set of ions **78a-g** of the first seven-ion portion **70** and the second set of ions **78a-g** of the second seven-ion portion **70** are configured to be fully connected to one another and/or to ions of neighboring qubit gates (e.g., simultaneously, or in any subset combination) (dotted lines denoting entanglements among the first set of ions **78a-g** and the second set of ions **78a-g** are omitted from FIG. 2F for the sake of clarity).

(65) The six ions **78a-f** in the “base” are an example of six qubits arranged substantially in a first substantially planar region **552** (e.g., the distances of the six ions **78a-f** from the substrate portion **72** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another; at a distance H.sub.1 of about 40 microns from the substrate portion **72**), the six ions **78a-f** in the “cap” are an example of six qubits arranged substantially in a second substantially planar region **554** (e.g., the distances of the six ions **78a-f** from the substrate portion **72** can be within ± 5 microns, within ± 2 microns, and/or within ± 1 micron of one another; at a distance H.sub.1 of about 40 microns from the substrate portion **72**) substantially parallel to the first substantially planar region **552**, one ion **78g** above the base is an example of a qubit arranged in a third substantially planar region **556** substantially parallel to the first substantially planar region **552** (e.g., at a distance H.sub.2 in a range of 30 microns to 40 microns from the substrate portion **72**), and one ion **78g** below the cap is an example of a qubit arranged in a fourth substantially planar region **558** substantially parallel to the second substantially planar region **554** (e.g., at a distance H.sub.3 in a range of 50 microns to 60 microns from the substrate portion **72**). The qubits of the first substantially planar region **552** are configured to interact with one another, the qubits of the second substantially planar region **554** are configured to interact with one another and with qubits of the first substantially planar region **552**. The qubit of the third substantially planar region **556** is configured to interact with the qubits of the first substantially planar region **552** and with the qubits of the second substantially planar region **554**. The qubit of the fourth substantially planar region **558** is configured to interact with qubits of the first substantially planar region **552**, with qubits of the second substantially planar region **554**, and with the qubit of the third substantially planar region **556** in accordance with certain implementations described herein. In certain implementations, the first set of ions **78a-g** and/or the second set of ions **78a-g** are further configured to interact with ions of other qubit gates neighboring the fourteen-ion qubit gate **550** (e.g., intercell interactions).

(66) The examples provided correspond to configurations configured to be employed in the pluralities of multi-qubit gate array implementations that follow (e.g., as QFPGA or QASIC

implementations) for ease of discussion. Other cell combinations of the “cap” and “base” are also compatible with certain implementations described herein. For example, in a QASIC implementation, it can be advantageous to combine the seven-ion portion **70** of FIG. 2B, modified by an increase or decrease in length of the electropotential well **77g**, and concomitant distance of the ion **78g** from the electrode region **76g** as described above, to create a fourteen-ion qubit gate that can be used up to a C.sup.13NOT/C.sup.13 ϕ gate as schematically illustrated in FIG. 2F. In addition, these and other numbers of qubits (e.g., 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, or more qubits) per first portion **810** and/or per second portion **820** are compatible with certain implementations described herein.

(67) Certain implementations described herein provide a quantum computing (QC) system **1000** comprising a substantially planar first substrate **600** and a substantially planar second substrate **700**, the first substrate **600** and the second substrate **700** substantially parallel to one another. The quantum computing system **1000** further comprises a multiple-qubit gate array **800** comprising a plurality of multiple-qubit gates **802** positioned in a region between the first substrate **600** and the second substrate **700**. Each multiple-qubit gate **802** of the array **800** comprises a first (e.g., base) portion **810** at (e.g., above; below; on) a surface of the first substrate **600** and a second (e.g., cap) portion **820** at (e.g., above; below; on) a surface of the second substrate **700** and the qubits interact with one another between the surfaces of the first and second substrates **600**, **700**. The first portion **810** of each multiple-qubit gate **802** of the array **800** is selected from the group consisting of: a single-qubit portion **10**, a three-qubit portion **30**, a six-qubit portion **50**, and a seven-qubit portion **70**. The first portions **810** are arranged along the surface of the first substrate **600** (e.g., the substrate regions **12**, **32**, **52**, **72** of the single-qubit portions **10**, three-qubit portions **30**, six-qubit portions **50**, and seven-qubit portions **70** are regions of the first substrate **600**). The second portion **820** of each multiple-qubit gate **802** of the array **800** is selected from the group consisting of: a single-qubit portion **10**, a three-qubit portion **30**, a six-qubit portion **50**, and a seven-qubit portion **70**. The second portions **820** are arranged along the surface of the second substrate **700** (e.g., the substrate regions **12**, **32**, **52**, **72** of the single-qubit portions **10**, three-qubit portions **30**, six-qubit portions **50**, and seven-qubit portions **70** are regions of the second substrate **700**). For each multiple-qubit gate **802**, each qubit of the first portion **810** and of the second portion **820** of the multiple-qubit gate **802** is configured to be quantum-mechanically entangled with each of the other qubits of the first portion **810** and the second portion **820** of the multiple-qubit gate **802**.

(68) FIG. 3A schematically illustrates a top view of four example first portions **810** (e.g., bases) of an example array **800** comprising four multiple-ion qubit gates (e.g., cells) **802** in accordance with certain implementations described herein. The four first portions **810** of FIG. 3A comprise a one-ion portion **10**, a three-ion portion **30**, a six-ion portion **50**, and a seven-ion portion **70**. These four first portions **810** are tiled together with their respective substrate regions **12**, **32**, **52**, **72** each part of a common first substrate **600** (e.g., the substrate regions **12**, **32**, **52**, **72** are coplanar with one another at a surface of the first substrate **600**). The tiling includes a rhomboid region **830** bounded by the four first portions **810**. As shown in FIG. 3A, at least some of the electrode regions of the six-ion portion **50** and the seven-ion portion **70** (e.g., electrode regions **56a-f**, **76a-f**) extend to neighboring first portions **810** and/or the rhomboid region **830**. In certain implementations, the first portions **810** in adjacent rows are configured to facilitate tiling the first portions **810** close together (e.g., without the electrode regions overlapping one another). While FIG. 3A shows the first portions **810** in a substantially rectangular pattern, the first portions **810** of other implementations can be in a substantially hexagonal pattern or a substantially diagonal pattern. Furthermore, while the first portions **810** of FIG. 3A are schematically illustrated as a 2×2 array, other tiling combinations of two, three, or more portions in arrays are also compatible with certain implementations described herein. For example, the first portions **810** can be tiled in arrays that are linear (e.g., 1×2, 1×3, or more), square or rectangular (e.g., 2×3, 3×3, 2×4, 3×4, 4×4, 2×5, etc.), and other geometries that can be regular or irregular (e.g., similar to domino tiling) and/or

symmetric or non-symmetric.

(69) FIG. 3B schematically illustrates a top view of four example second portions **820** (e.g., caps) of the example array **800** and four multiple-ion qubit gates **802** in accordance with certain implementations described herein. The four second portions **820** of FIG. 3B comprise a one-ion portion **10**, a three-ion portion **30**, a six-ion portion **50**, and a seven-ion portion **70**. These four second portions **820** are tiled together with their respective substrate regions **12**, **32**, **52**, **72** each part of a common second substrate **700** (e.g., the substrate regions **12**, **32**, **52**, **72** are coplanar with one another at a surface of the second substrate **700**). The tiling includes a rhomboid region **840** bounded by the four first portions **820**. As shown in FIG. 3B, at least some of the electrode regions of the six-ion portion **50** and the seven-ion portion **70** (e.g., electrode regions **56a-f**, **76a-f**) extend to neighboring second portions **820** and/or the rhomboid region **840**. In certain implementations, the second portions **820** in adjacent rows are configured to facilitate tiling the second portions **820** close together (e.g., without the electrode regions overlapping one another). While FIG. 3B shows the second portions **820** in a substantially rectangular pattern, the second portions **820** of other implementations can be in a substantially hexagonal pattern or a substantially diagonal pattern. Furthermore, while the second portions **820** of FIG. 3B are schematically illustrated as a 2×2 array, other tiling combinations of two, three, or more portions in arrays, and which coincide with the tiling of the first portions **810**, are also compatible with certain implementations described herein. For example, the second portions **820** can be tiled in arrays that are linear (e.g., 1×2, 1×3, or more), square or rectangular (e.g., 2×3, 3×3, 2×4, 3×4, 4×4, 2×5, etc.), and other geometries that can be regular or irregular (e.g., similar to domino tiling) and/or symmetric or non-symmetric.

(70) FIGS. 3C-3D schematically illustrates an exploded view and a top overlay view, respectively, of the example array **800** and four multiple-ion qubit gates **802** of FIGS. 3A-3B in accordance with certain implementations described herein. The four multiple-ion qubit gates **802** comprise two four-ion qubit gates **100** and two thirteen-ion qubit gates **500** between the first substrate **600** and the second substrate **700**. One of the four-ion qubit gates **100** comprises a three-ion base portion **30** and a one-ion cap portion **10**, another of the four-ion qubit gates **100** comprises a one-ion base portion **10** and a three-ion cap portion **30**, one of the thirteen-ion qubit gates **500** comprises a seven-ion base portion **70** and a six-ion cap portion **50**, and another of the thirteen-ion qubit gates **500** comprises a six-ion base portion **50** and a seven-ion cap portion **70**. As described herein with regard to FIGS. 3A and 3B, other tiling combinations of the bases and caps into 3-D gate cell layouts can be used.

(71) FIG. 3E schematically illustrate an exploded view of another example array **800** with four multiple-ion qubit gates **802** in accordance with certain implementations described herein. The four multiple-ion qubit gates **802** comprise four ten-ion qubit gates **450** between the first substrate **600** and the second substrate **700**. Two of the ten-ion qubit gates **450** each comprises a three-ion base portion **30** and a seven-ion cap portion **70**, and the other two ten-ion qubit gates **450** each comprises a seven-ion base portion **70** and a three-ion cap portion **30**. In the 2×2 array of the substrate **600**, the three-ion base portions **30** and seven-ion base portions **70** alternate with one another and in the 2×2 array of the substrate **700**, the seven-ion cap portions **70** and three-ion cap portions **30** alternate with one another. The electrical trace line layouts shown in FIG. 3E are different from those of FIGS. 3C-3D.

(72) FIGS. 4A-4B schematically illustrate an exploded view and a top overlay view, respectively, of an example array **900** comprising sixteen multiple-ion qubit gates **902** in a 4×4 array in accordance with certain implementations described herein. Other multi-qubit gate arrays with different numbers of qubit gate arrays (e.g., more than sixteen) and/or in different geometric configurations (e.g., linear; rectangular; square; regular; irregular; symmetric; non-symmetric) are also compatible with certain implementations described herein. The sixteen multiple-ion qubit gates **902** of the array **900** are arranged substantially in a rectangular pattern with four rows each having four multiple-ion qubit gates **902** and four columns each having four multiple-ion qubit

gates **902**. The multiple-ion qubit gates **902** of each row comprise two four-ion qubit gates **100** and two thirteen-ion qubit gates **500** arranged alternately (e.g., “4-13-4-13”) and the multiple-ion qubit gates **902** of each column comprise two four-ion qubit gates **100** and two thirteen-ion qubit gates **500** arranged alternately (e.g., “4-13-4-13”). The first (e.g., base) portions **810** of the array **900** are arranged such that any four nearest-neighboring first portions **810** comprise a one-ion portion **10**, a three-ion portion **30**, a six-ion portion **50**, and a seven-ion portion **70**, and the second (e.g., cap) portions **820** of the array **900** are arranged such that any four nearest-neighboring second portions **820** comprise a one-ion portion **10**, a three-ion portion **30**, a six-ion portion **50**, and a seven-ion portion **70**. In certain implementations, the layouts of the first portions **810** and second portions **820** of the array **900** (e.g., for a QFPGA) are configured to reduce (e.g., minimize) qubit-to-qubit spacing and/or to optimize cell-to-cell connectivity.

(73) As schematically illustrated in FIGS. **4A-4B**, at least some of the electrical traces **14** extending along the first substrate **600** and/or the second substrate **700** comprise substantially straight sections that are substantially perpendicular to the boundaries between neighboring first portions **810** of the first substrate **600** and/or the boundaries between neighboring second portions **820** of the second substrate **700**. For example, the electrical traces **14** shown as being vertical in FIG. **4B** are substantially perpendicular to the horizontal boundaries in FIG. **4B**. FIG. **4C** schematically illustrates a top overlay view of another example multiple-ion qubit gate array **900** with sixteen multiple-ion qubit gates **902** in accordance with certain implementations described herein. At least some of the electrical traces **14** extending along the first substrate **600** and/or the second substrate **700** in FIG. **4C** comprise substantially straight section that are not substantially perpendicular to the boundaries between neighboring first portions **810** of the first substrate and/or the boundaries between neighboring second portions **820** of the second substrate **700**. For example, the electrical traces **14** shown as being substantially vertical in FIG. **4C** extend over at least some of the hexagonal boundaries in FIG. **4C** but are not substantially perpendicular to these hexagonal boundaries. Other positions and/or orientations of the electrical traces **14** are also compatible with certain implementations described herein. For example, the electrical traces **14** can be curved so as to create room for optical ports for entry and/or exit of laser signals into the region between the first substrate **600** and the second substrate **700**.

(74) FIG. **4D** schematically illustrates a top overlay view of another example multiple-ion qubit gate array **800** comprising four multiple-ion qubit gates **802** in accordance with certain implementation described herein. The four multiple-ion qubit gates **802** comprise two eight-ion qubit gates **300** (see, e.g., FIG. **2B**) and two nine-ion qubit gates **400** (see, e.g., FIG. **2C**) between the first substrate **600** and the second substrate **700**. One of the eight-ion qubit gates **300** comprises a seven-ion base portion **70** and a one-ion cap portion **10**, another of the eight-ion qubit gates **300** comprises a one-ion base portion **10** and a seven-ion cap portion **70**, one of the nine-ion qubit gates **400** comprises a three-ion base portion **30** and a six-ion cap portion **50**, and another of the nine-ion qubit gates **400** comprises a six-ion base portion **50** and a three-ion cap portion **30**.

(75) FIG. **4E** schematically illustrates a top overlay view of another example multiple-ion qubit gate array **900** comprising sixteen multiple-ion qubit gates **902** in accordance with certain implementations described herein. The sixteen multiple-ion qubit gates **902** of the array **900** are arranged substantially in a rectangular pattern with four rows each having four multiple-ion qubit gates **902** and four columns each having four multiple-ion qubit gates **902**. The rows of the multiple-ion qubit gates **902** are arranged alternately between four nine-ion qubit gates **400** (e.g., 9-9-9-9) and four eight-ion qubit gates **300** (e.g., “8-8-8-8”) and the multiple-ion qubit gates **902** of each column comprise two nine-ion qubit gates **400** and two eight-ion qubit gates **300** arranged alternately (e.g., “9-8-9-8”). In certain implementations, the layouts of the first portions **810** and second portions **820** of the array **900** (e.g., for a QFPGA) are configured to provide consistent spacing between ions of neighboring first portions **810** and second portions **820** of the array **900**.

(76) FIGS. **4F-4G** schematically illustrate an exploded view and a top overlay view, respectively, of

another example array **900** comprising sixteen multiple-ion qubit gates **902** in a 4×4 array in accordance with certain implementations described herein. The sixteen multiple-ion qubit gates **902** of the array **900** are arranged substantially in a rectangular pattern with four rows each having four multiple-ion qubit gates **902** and four columns each having four multiple-ion qubit gates **902**. The multiple-ion qubit gates **902** of each row comprise four ten-ion qubit gates **450** and the multiple-ion qubit gates **902** of each column comprise four ten-ion qubit gates **450**. The rows and columns of the first (e.g., base) portions **810** of the array **900** comprise three-ion portions **30** and seven-ion portions **70** arranged alternately (e.g., “3-7-3-7”), and the rows and columns of the second (e.g., cap) portions **820** of the array **900** are arranged alternately (e.g., “3-7-3-7”). In certain implementations, the layouts of the first portions **810** and second portions **820** of the array **900** are configured to provide more uniform spacing.

(77) FIGS. 5A-5I schematically illustrate various views of portions of example QC structures **1000** in accordance with certain implementations described herein. The example QC structure **1000** can be used in a QASIC or a QFPGA layout. In certain implementations, the QC structure **1000** advantageously provides sufficient space for cooling systems and magnetic field systems for operating the QC structure **1000**. In certain implementations, the overall configuration preserves channel space for electrical traces to control multiple electrodes per electrode region while advantageously addressing the problem of electrode overlap, which occurs between adjacent qubit gates in two-dimensional (2-D) layouts if they are tiled closely together (e.g., in an attempt to preserve usable coherence).

(78) The example QC structure **1000** comprises the example array **900** of FIG. 4C and with electrical traces **14** that are similar to those of FIG. 4C. In certain implementations, the alternating inverted cell rows of the base and/or cap portions of the array **900** facilitate formation of electrical channels through which electrical signals can be provided to the ion traps of the array **900**. For example, as shown in FIG. 5A, the electrical traces **14** are configured to provide electrical signals to the various electrodes of the ion traps. Other configurations of the cell rows and columns, electrical traces, as well as cells with other numbers of ions and/or qubits are also compatible with certain implementations described herein.

(79) In certain implementations, the alternating inverted cell rows of the base and/or cap portions of the array **900** facilitate formation of optical channels through which optical signals can be inputted to and/or outputted from the ion traps of the array **900**. The example QC structure **1000** further comprises a plurality of optical ports **905** in accordance with certain implementations described herein. The plurality of optical ports **905** of the example QC structure **1000** comprises a first plurality of optical ports **910** in optical communication with a first plurality of optical fibers **912**, the first plurality of optical ports **910** within the first portions **810** of the first substrate **600**. The plurality of optical ports **905** of the example QC structure **1000** further comprises a second plurality of optical ports **920** in optical communication with a second plurality of optical fibers **922**, the second plurality of optical ports **920** within the second portions **820** of the second substrate **700**. At least some of the optical ports **910** are configured to emit optical signals **914** (e.g., pulses generated by one or more lasers, not shown) configured to irradiate specific ions of the array **900** (e.g., for addressing and/or controlling specific qubits of the array **900**) and at least some of the optical ports **920** are configured to emit optical signals **924** (e.g., pluses generated by one or more lasers, not shown) configured to irradiate specific ions of the array **900** (e.g., for addressing and/or controlling specific qubits of the array **900**). The plurality of optical ports **905** of the example QC structure **1000** further comprises a third plurality of optical ports **930** and a third plurality of optical fibers **932**. The optical ports **930** can be in optical communication with the third plurality of optical fibers **932**, the third plurality of optical ports **930** positioned outside a periphery of the array **900** and configured to emit optical signals **934** (e.g., pulses generated by one or more lasers, not shown), the optical signals **934** configured to irradiate specific ions of the array **900** (e.g., for addressing and/or controlling specific qubits of the array **900**). In certain implementations, the optical ports **910**, **920**,

930 comprise polished fiber ends configured to direct laser light signals **914, 924, 934** towards the corresponding specific ions of the array **900**.

(80) The plurality of optical ports **905** of the example QC structure **1000** further comprises a fourth plurality of optical exit ports **940** within the first portions **810** and/or the second portions **820** and configured to allow light from the optical signals **914, 924** passing the irradiated specific ions to exit or to be absorbed, so as to reduce (e.g., minimize) cross-talk or other noise from light reflection or scattering towards unintended qubits. The optical exit ports **940** can comprise holes and/or light absorptive material.

(81) The example QC structure **1000** further comprises a plurality of optical detectors **950** in optical communication with a fourth plurality of optical fibers **952**. The plurality of optical detectors **950** (e.g., charge-coupled device (CCD) cameras; superconducting single-photon nanowire detectors (SNSPDs); photomultiplier tubes (PMTs); bolometers) are configured to receive optical signals (e.g., fluorescent light **926**) from ions of the array **900** for reading out the status of the qubits of the array **900**.

(82) FIG. 5A schematically illustrates a top view of the first portions **810** of the example array **900** on the first substrate **600**, with the second substrate **700** removed. As shown in FIG. 5A, the electrical traces **14** can extend along the array **900** to provide electrical connectivity to the various electrodes of the first portions **810**. The optical ports **910** can be positioned (e.g., interleaved) within the first portions **810** and oriented such that the optical signals **914** are directed towards specific ions of the second portions **820**.

(83) FIGS. 5B-5C schematically illustrate a perspective view and a side view, respectively, of the example QC structure **1000**, including both the first and second substrates **600, 700** (e.g., multi-chip structure) of the example QC structure **1000**.

(84) FIG. 5D schematically illustrates a perspective view (without the second substrate **700**) and a side view (with both the first substrate **600** and the second substrate **700**) of the example QC structure **1000** with the optical signals **934** emitted from the third plurality of optical ports **930**. These optical signals **934** are directed to ions **904** positioned at the center of the multiple-ion qubit gates **902**, which are at a different distance from the first substrate **600** and the second substrate **700** than are the other non-center ions **906** of the multiple-ion qubit gates **902**.

(85) FIG. 5E schematically illustrates a perspective view (without the optical signals **914, 924**), FIGS. 5F-5G schematically illustrate two side views of the example QC structure **1000**, and FIG. 5H schematically illustrates another side view of the example QC structure **1000** in accordance with certain implementations described herein. FIG. 5F shows three of the optical signals **914** emitted from three of the first plurality of optical ports **910**, each of the three optical signals **914** directed to a corresponding ion of the second portion **820** (e.g., a six-ion portion **50**) of the multiple-ion qubit gate **902**. In addition, FIG. 5F shows the optical signals **934** emitted from the third plurality of optical ports **930**. FIG. 5G shows six of the optical signals **914** emitted from six of the first plurality of optical ports **910**, each of the six optical signals **914** directed to a corresponding ion of the second portion **820** (e.g., a six-ion portion **50**) of the multiple-ion qubit gate **902**. In addition, FIG. 5G shows the optical signals **934** emitted from the third plurality of optical ports **930** and six of the optical signals **924** emitted from six of the second plurality of optical ports **920**, each of the six optical signals **924** directed to a corresponding ion of the first portion **810** (e.g., a seven-ion portion **70**) of the multiple-ion qubit gate **902**. FIG. 5H shows the optical signals **924** emitted from the second plurality of optical ports **920** to irradiate corresponding ions, with some of the light from the optical signals **924** being allowed to exit via corresponding optical exit ports **940** (e.g., exiting the region between the first and second substrates **600, 700**; being subsequently detected and/or absorbed).

(86) FIG. 5I schematically illustrates a side view of the example QC structure **1000** of FIG. 5C-5D, with an additional row of optical ports **930** for emitting optical signals **934**. For example, as shown in FIG. 5I, the back supports have two rows of optical ports **930** and one row of optical detectors

950, while the front supports have one row of optical ports **930** and two rows of optical detectors **950**. In certain implementations, a plurality of optical signals can be used advantageously to utilize a plurality of ion species and to perform gate operations that are optimally suited to each ion species. The type of optical addressing and transitions employed to address, initialize and/or perform quantum gate operations on one or more ions can depend on the ion species used. For example, certain ion species can be addressed using single optical wavelength transitions and can be referred to as “optical qubits” (e.g., $^{40}\text{Ca}^+$). In certain implementations, at least one optical signal **934** is used to illuminate a plurality of ions **904** (e.g. to initialize or reset their qubit states to the lowest energy, ground state). In certain implementations, at least one optical signal **934** is used to entangle a plurality of ions **904** and to perform certain quantum gate operations involving one or more ions. Certain other ion species can have hyperfine states and can be referred to as “hyperfine qubits” (e.g. $^{43}\text{Ca}^+$; $^{171}\text{Yb}^+$ and others); these typically employ two lasers in Raman transitions. In certain implementations, optical signals **934** of two different wavelengths are used advantageously to address and perform quantum gate operations on one or more ions.

(87) FIG. **6A** schematically illustrates a top overlay view of an example 4×4 array **900** of alternating four-ion qubit gates **100** and thirteen-ion qubit gates **500** with a plurality of optical ports **905** in accordance with certain implementations described herein. The array **900** shown in FIG. **6A** is an example of a QFPGA layout. At least some of the optical ports **910**, **920** (denoted in FIG. **6A** by white circles) are configured to emit optical signals **914**, **924** into the region between the first substrate **600** and the second substrate **700** and at least some of the optical exit ports **940** (denoted in FIG. **6A** by dark circles) are configured to allow the optical signals **914**, **924** to exit and/or to be absorbed. The optical exit ports **940** in certain implementations are configured to prevent reflections of the optical signals **914**, **924** from interfering or otherwise degrading performance of the example QC structure **1000**. For example, the optical exit ports **940** can comprise optical absorbers. At least some of the optical ports **910**, **920** and optical exit ports **940** can be positioned within the hexagonal first portions **810** and second portions **820** of the multiple-ion qubit gates **902**, while at least some of the optical exit ports **940** can be positioned in the rhomboid regions **830**, **840** between the hexagonal first and/or second portions **810**, **820**. For example, as shown in FIG. **6A**, at least some of the optical ports **910**, **920** and the optical exit ports **940** are positioned between the “petal-shaped” electrode regions **16** and some of the optical exit ports **940** are positioned in the rhomboid regions **830**, **840**.

(88) FIGS. **6B-6D** schematically illustrate optical signals irradiating the ions of the array **900** of FIG. **6A** in accordance with certain embodiments described herein. In each of FIGS. **6B-6D**, the center ions of the four-ion qubit gate **100**, the seven-ion qubit gate **200**, and the thirteen-ion qubit gate **500** can be a laser-addressed and/or manipulated (e.g., target) ion and can be irradiated by optical signals from the optical ports **930** positioned outside a periphery of the array **900**. The other ions of the four-ion qubit gate **100**, the seven-ion qubit gate **200**, and the thirteen-ion qubit gate **500** can be laser addressed (e.g., control) ions.

(89) As shown in FIG. **6B**, three of the optical ports **910** emit optical signals **914** which irradiate three corresponding ions of a four-ion qubit gate **100** and three of the optical exit ports **940** allow portions of the optical signals **914** passing the three corresponding ions to exit in order to reduce (e.g., minimize) light reflection or scattering within the array **900**. In certain implementations, using the four-ion qubit gate **100** as a native $C.^{3}\text{NOT}$ gate, a single gate operation can advantageously exploit geometric symmetry and replace scores of 1- and 2-qubit gate operations, faster and with fewer aggregated errors.

(90) As shown in FIG. **6C**, six of the optical ports **910** emit optical signals **914** which irradiate six corresponding ions of a seven-ion qubit gate **200** and six of the optical exit ports **940** allow portions of the optical signals **914** passing the six corresponding ions to exit in order to reduce (e.g., minimize) light reflection or scattering within the array **900**. In certain implementations, using the seven-ion qubit gate **200** as a native $C.^{6}\text{NOT}$ gate, a single gate operation can advantageously

exploit geometric symmetry and replace hundreds of 1- and 2-qubit gate operations, faster and with fewer aggregated errors.

(91) As shown in FIG. 6D, six of the optical ports **910** emit optical signals **914** and six of the optical ports **920** emit optical signals **924** which irradiate twelve corresponding ions of the thirteen-ion qubit gate **500** and twelve of the optical ports **940** allow portions of the optical signals **914**, **924** passing the twelve corresponding ions to exit in order to reduce (e.g., minimize) light reflection or scattering within the array **900**. In certain implementations, using the thirteen-ion qubit gate **500** as a native C.sup.12NOT gate, a single gate operation can advantageously exploit geometric symmetry and replace thousands of 1- and 2-qubit gate operations, faster and with fewer aggregated errors.

(92) FIG. 6E schematically illustrates top views of the base portions and an overlay of the base and cap portions of an example 4×4 array **900** of ten-ion qubit gates **450** with a plurality of ion loading holes and optical ports **910**, **920** in accordance with certain implementations described herein. The base portions comprises eight three-ion portions **30** and eight seven-ion portions **70** alternately arranged with one another, and the cap portions comprises eight three-ion portions **30** and eight seven-ion portions **70** alternately arranged with one another (see, e.g., FIGS. 4C, 4F, 4G).

(93) FIG. 6F schematically illustrates an overlay of the base and cap portions of an example 4×4 array **900** of ten-ion qubit gates **450** with a plurality of microwave antenna regions **942** located on at least one chip substrate **600**, **700** in accordance with certain implementations described herein. Depending the particular species of qubit(s) used (e.g., if the qubits include hyperfine qubit states, such as .sup.9Be+; .sup.43Ca+; .sup.171Yb+ and many others), certain implementations described herein advantageously provide microwave addressing and control of the trapped ions in addition to or in lieu of certain optical methods (see e.g., C. Ospelkaus et al., Phys Rev. Lett. Vol 101, 090502 (2008); T. P. Harty et al., Phys Rev. Lett. Vol. 113, 220501 (2014)).

(94) FIG. 7A schematically illustrates a side view of a portion of an example QC structure **1000** and FIG. 7B schematically illustrates a close-up view of a smaller portion of the QC structure **1000** of FIG. 7A in accordance with certain implementations described herein. As shown in FIG. 7A, optical signals **924** (e.g., light having a laser wavelength from ion-addressing lasers via the optical fibers **912**, **922**) emitted from the optical ports **910**, **920** is directed to irradiate corresponding ions **18**, **38**, **58**, **78**. In response to the optical signals **924**, the ions **18**, **38**, **58**, **78** can fluoresce and emit fluorescent light **926**. In certain implementations, the ion fluorescence wavelength can be at or near the laser wavelength of the optical signals **924**, while in certain other implementations, the ion fluorescence wavelength is different from the laser wavelength of the optical signals **924**. The light propagating to and passing through the optical exit ports **940** can comprise a mixture of the fluorescent light **926** from the irradiated ions **18**, **38**, **58**, **78** and the optical signals **924** emitted from the optical ports **910**, **920**, as shown in FIG. 7B.

(95) In certain implementations, as schematically illustrated by FIGS. 7A and 7B, the QC structure **1000** comprises at least one light-selective layer **1100** configured to separate the optical signal **924** from the fluorescent light **926**. For example, as shown in FIGS. 7A and 7B, at least one light-selective layer **1100** comprises a wavelength-selective material positioned between the optical exit port **940** and the corresponding optical detector **950**, and is configured to prevent (e.g., deflect; divert; refract; reflect; diffract) the optical signals **924** from reaching the optical detector **950** while allowing fluorescent light **926** to reach the optical detector **950** (e.g., to pass directly to the optical detector **950**). Examples of light-selective layers **1100** configured to separate the optical signal **924** from the fluorescent light **926** in accordance with certain implementations described herein include but are not limited to: layers with wavelength-dependent refractive indices, prism-like layers, and diffraction gratings. In certain other implementations, at least one light-selective layer **1100** comprises a polarization-selective material (e.g., polarizing filter; birefringent crystal lattice) and/or a phase-selective material (e.g., quarter-wave plate; highly dispersive material; prism-like layer) configured to prevent (e.g., due to being orthogonally polarized and/or out of phase with) the

optical signals **924** from reaching the optical detector **950** while allowing the fluorescent light **926** to reach the optical detector **950**. In certain such implementations, the light-selective layer **1100** can reduce the intensity of the fluorescent light **926** by an allowable amount (e.g. approximately one-half; -3 dB) since the fluorescent light **926** comprises photons of random polarization and/or phases, half of which pass the light-selective layer **1100** whereas the optical signals **924** are blocked or highly attenuated resulting in a favorable signal to noise ratio of fluorescent light **926** reaching the optical detector **950**. In certain implementations, the use of light-selective layers **1100** can be used in conjunction with pulse-timing of the optical signals **924** and gating the optical detector **950** readout to further increase signal-to-noise detection of fluorescent light **926** signals against the optical signals **924**.

(96) FIGS. 7C and 7D schematically illustrate two views of another example QC structure **1000** in accordance with certain implementations described herein. As schematically illustrated by FIGS. 7C and 7D, the QC structure **1000** has the optical exit ports **940** and the optical detectors **950** are positioned such that (i) optical signals **924a** used to irradiate a first predetermined ion **928a** propagate through a corresponding optical exit port **940** while not reaching the optical detector **950** corresponding to the optical exit port **940** and (ii) fluorescent light **926** from a second predetermined ion **928b** propagates from the ion **928b** through the optical exit port **940** to the corresponding optical detector **950** while the optical signals **924** (e.g., either irradiating the ion **924b** or other ions) do not propagate through the optical exit port **940** to the corresponding optical detector **950**. For example, certain such configurations can be useful for QC structures **1000** in which the fluorescent light **926** and the optical signals **924** are not readily distinguishable from one another (e.g., by wavelength, polarization, and/or phase).

(97) FIG. 7E schematically illustrates a side view of a portion of an example QC structure **1000** comprising ion loading holes **1200** (e.g., vertical interconnects (VIAs), through-silicon vias (TSVs); carbon nanotube (CNT) structures) and single-ion optical detectors **1210** (e.g., charge-coupled devices (CCDs); PMTs; SNSPDs; bolometers) in accordance with certain implementations described herein. In certain implementations, the ion loading holes **1200** are configured to introduce the ions **18**, **38**, **58**, **78** into the corresponding electropotential wells **17**, **37**, **57**, **77** and to be controllably opened and/or closed in response to signals from a corresponding single-ion optical detector **1210**. For example, upon the single-ion optical detector **1210** detecting that a single ion has passed through the corresponding ion loading hole **1200**, the single-ion optical detector **1210** can close the ion loading hole **1200** so that additional ions do not pass through. Upon the corresponding electropotential well **17**, **37**, **57**, **77** not containing an ion **18**, **38**, **58**, **78**, the single-ion optical detector **1210** can open the ion loading hole **1200** so that a single ion **18**, **38**, **58**, **78** is supplied to the electropotential well **17**, **37**, **57**, **77**.

(98) FIG. 8 schematically illustrates a side view of an example QC structure **1000** having an example 16×16 cell array **1300** (left-side of FIG. 8A) and a top projection view of the 16×16 cell array **900** (right-side of FIG. 8) in accordance with certain implementations described herein. The 16×16 cell array **1300** of FIG. 8 comprises sixteen of the 4×4 cell arrays **900** of FIGS. 5A-5D tiled with one another. As shown in the right-side of FIG. 8, the 16×16 cell array **1300** can be scaled to an area of about one-quarter square centimeter (0.25 cm^2) on nominal one square centimeter (1 cm^2) substrates **600**, **700**. For example, the 16×16 cell array **1300** can have alternating 4-ion gate arrays **100** and thirteen-ion gate arrays **500** to enable 16,437 qubits within the area of the substrates **600**, **700** (e.g., using inter-trap spacings on the order of 40 microns). For another example, the 16×16 cell array **1300** can include only 10-ion gate arrays **450** to enable 19,400 qubits within the area of the substrates **600**, **700** (e.g., using inter-trap spacings on the order of 40 microns).

(99) If the QC structure **100** comprises a cell array having a larger number of cells and extending over a larger area, the number of qubits can be increased. For example, a cell array having alternating 4-ion gate arrays **100** and thirteen-ion gate arrays **500** across an area of 1 cm^2 can

enable 65,750 qubits per square centimeter (e.g., using inter-trap spacings on the order of 40 microns) and a cell array having only 10-ion gate arrays **450** across the area of 1 cm.^{sup.2} can enable over 77,000 qubits per square centimeter (e.g., using inter-trap spacings on the order of 40 microns).

(100) FIG. **9** shows four tables comparing the total number of qubits for various 4×4 cell arrays in accordance with certain implementations described herein and examples of how reconfigurability of the arrays advantageously enables multiple complementary attributes to be selected. As shown in FIG. **9**, for a 4×4 cell array having alternating eight 4-ion gate arrays **100** and eight 13-ion gate arrays **500** (e.g., denoted “QFPGA I” in FIG. **9**), the total number of qubits is 136. This represents a relatively low qubit density within the overall trade space yet the interspersal of extra high capacity gates with adjacent lower capacity gates presents opportunities for error correction be performed efficiently in situ and/or for running algorithms that benefit from multiply-controlled NOT or multiply-controlled phase gates with large numbers of (e.g. 10 or more) controls. For a 4×4 cell array having six 4-ion gate arrays **100**, seven 10-ion gate arrays **450**, and three 13-ion gate arrays **500** (e.g., denoted “QASIC I in FIG. **9**), the total number of qubits is 133. However, for an example ASIC-type usage (e.g., where a few C.^{sup.12}NOT gates are used but greater relay speed or throughput across the array is desired), QASIC I can be more efficient than QFPGA I despite having three fewer qubits in its array. For a 4×4 cell array having sixteen 10-ion gate arrays **450** (e.g., denoted “QFPGA II” in FIG. **9**), the total number of qubits is 160. This is the highest qubit density presented for an array, with the most efficient throughput across all directions and the most uniform design. For a 4×4 cell array having four 4-ion gate arrays **100**, ten 10-ion gate arrays **450**, and two 13-ion gate arrays **500** (e.g., denoted “QASIC II in FIG. **9**), the total number of qubits is 142. This is toward the middle of the range of qubit densities, nevertheless such an array could be advantageous in special ASIC-type uses in which a modest number of C.^{sup.12}NOT gates are used and the direction of highest relay speed or throughput can be predefined (e.g., from lower left to upper right and vice versa).

(101) The invention has been described in several non-limiting implementations. It is to be understood that the implementations are not mutually exclusive, and elements described in connection with one implementation may be combined with, rearranged, or eliminated from, other implementations in suitable ways to accomplish desired design objectives. No single feature or group of features is necessary or required for each implementation.

(102) For purposes of summarizing the present invention, certain aspects, advantages and novel features of the present invention are described herein. It is to be understood, however, that not necessarily all such advantages may be achieved in accordance with any particular implementation. Thus, the present invention may be embodied or carried out in a manner that achieves one or more advantages without necessarily achieving other advantages as may be taught or suggested herein.

(103) As used herein any reference to “one implementation” or “some implementations” or “an implementation” means that a particular element, feature, structure, or characteristic described in connection with the implementation is included in at least one implementation. The appearances of the phrase “in one implementation” in various places in the specification are not necessarily all referring to the same implementation. Conditional language used herein, such as, among others, “can,” “could,” “might,” “may,” “e.g.,” and the like, unless specifically stated otherwise, or otherwise understood within the context as used, is generally intended to convey that certain implementations include, while other implementations do not include, certain features, elements and/or steps. In addition, the articles “a” or “an” or “the” as used in this application and the appended claims are to be construed to mean “one or more” or “at least one” unless specified otherwise.

(104) Language of degree, as used herein, such as the terms “approximately,” “about,” “generally,” and “substantially,” represent a value, amount, or characteristic close to the stated value, amount, or characteristic that still performs a desired function or achieves a desired result. For example, the

terms “approximately,” “about,” “generally,” and “substantially” may refer to an amount that is within $\pm 10\%$ of, within $\pm 5\%$ of, within $\pm 2\%$ of, within $\pm 1\%$ of, or within $\pm 0.1\%$ of the stated amount. As another example, the terms “generally parallel” and “substantially parallel” refer to a value, amount, or characteristic that departs from exactly parallel by ± 10 degrees, by ± 5 degrees, by ± 2 degrees, by ± 1 degree, or by ± 0.1 degree, and the terms “generally perpendicular” and “substantially perpendicular” refer to a value, amount, or characteristic that departs from exactly perpendicular by ± 10 degrees, by ± 5 degrees, by ± 2 degrees, by ± 1 degree, or by ± 0.1 degree. The ranges disclosed herein also encompass any and all overlap, sub-ranges, and combinations thereof. Language such as “up to,” “at least,” “greater than,” “less than,” “between,” and the like includes the number recited. As used herein, the meaning of “a,” “an,” and “said” includes plural reference unless the context clearly dictates otherwise. Also, as used in the description herein, the meaning of “in” includes “into” and “on,” unless the context clearly dictates otherwise.

(105) As used herein, the terms “comprises,” “comprising,” “includes,” “including,” “has,” “having” or any other variation thereof, are open-ended terms and intended to cover a non-exclusive inclusion. For example, a process, method, article, or apparatus that comprises a list of elements is not necessarily limited to only those elements but may include other elements not expressly listed or inherent to such process, method, article, or apparatus. Further, unless expressly stated to the contrary, “or” refers to an inclusive or and not to an exclusive or. For example, a condition A or B is satisfied by any one of the following: A is true (or present) and B is false (or not present), A is false (or not present) and B is true (or present), or both A and B are true (or present). As used herein, a phrase referring to “at least one of” a list of items refers to any combination of those items, including single members. As an example, “at least one of: A, B, or C” is intended to cover: A, B, C, A and B, A and C, B and C, and A, B, and C. Conjunctive language such as the phrase “at least one of X, Y and Z,” unless specifically stated otherwise, is otherwise understood with the context as used in general to convey that an item, term, etc. may be at least one of X, Y or Z. Thus, such conjunctive language is not generally intended to imply that certain implementations require at least one of X, at least one of Y, and at least one of Z to each be present.

(106) Thus, while only certain implementations have been specifically described herein, it will be apparent that numerous modifications may be made thereto without departing from the spirit and scope of the invention. Further, acronyms are used merely to enhance the readability of the specification and claims. It should be noted that these acronyms are not intended to lessen the generality of the terms used and they should not be construed to restrict the scope of the claims to the implementations described therein.

Claims

1. A quantum computing (QC) system comprising: a plurality of qubits arranged as a gate array comprising a plurality of gates each comprising (i) a cap comprising one or more first qubits and (ii) a base including one or more second qubits, the one or more first qubits of the cap and the one or more second qubits of the base (a) configured to be simultaneously entangled and (b) positioned between a first substrate and a second substrate.
2. The system of claim 1, further comprising: a plurality of substantially planar regions that are substantially parallel to one another wherein the plurality of qubits are arranged in the plurality of substantially planar regions such that a first substantially planar region comprises at least one qubit and a second substantially planar region comprising multiple qubits, wherein each gate comprises qubits at or near a surface of at least one of the first and second substrates.
3. The system of claim 1, wherein the first substrate is substantially planar and the second substrate is substantially planar.
4. The system of claim 1, wherein the base of each gate is at a surface of the first substrate and the cap of each gate is at a surface of the second substrate.

5. The system of claim 4, wherein the plurality of gates are arranged along the surface of the first substrate in a substantially rectangular lattice with at least one row and at least one column or in a substantially hexagonal lattice or in a substantially diagonal lattice.
6. The system of claim 5, wherein the substantially rectangular lattice comprises four rows each having four gates and four columns each having four gates.
7. The system of claim 6, wherein each row of the four rows comprises two gates each comprising four qubits and two gates each comprising thirteen qubits, the gates of the row arranged alternately and each column of the four columns comprises two gates each comprising four qubits and two gates each comprising thirteen qubits, the gates of the column arranged alternately.
8. The system of claim 7, wherein: the base of a first gate is adjacent to and in a first row with the base of a second gate and the base of a third gate is adjacent to the base of a fourth gate and in a second row adjacent to the first row, such that four nearest-neighboring bases comprise a base comprising one qubit, a base comprising three qubits, a base comprising six qubits, and a base comprising seven qubits, and the cap of each of the first, second, third, and fourth gates are arranged such that four nearest-neighboring caps comprise a cap comprising one qubit, a cap comprising three qubits, a cap comprising six qubits, and a cap comprising seven qubits.
9. The system of claim 4, wherein: the base of each gate of the gate array is selected from the group consisting of: a base comprising one qubit, a base comprising three qubits, a base comprising six qubits, and a base comprising seven qubits, and the cap of each gate of the gate array is selected from the group consisting of: a cap comprising one qubit, a cap comprising three qubits, a cap comprising six qubits, and a cap comprising seven qubits.
10. The system of claim 4, wherein, for each gate of the gate array, each qubit is configured to be quantum-mechanically entangled with at least two of the other qubits of the gate.
11. The system of claim 4, wherein the base of each gate of the array has 1, 2, 3, 4, 5, 6, or 7 qubits and the cap of each gate of the array has 1, 2, 3, 4, 5, 6, or 7 qubits.
12. The system of claim 2, wherein one or more qubits of one substantially planar region is configured to be directly entangled with the one or more qubits of at least one other substantially planar region to form 3-D cellular arrays configured to undergo operations in which more than two qubits participate simultaneously.
13. A quantum computing (QC) system comprising a plurality of qubit gates comprising a plurality of qubits configured to be fully connected and simultaneously entangled among one another, the plurality of qubit gates arranged in a lattice and each of the plurality of qubit gates configured to perform gate operations by simultaneous use of more than two qubits at a time.
14. The system of claim 13, wherein the lattice comprises a substantially rectangular lattice with at least one row and at least one column, a substantially hexagonal lattice, or a substantially diagonal lattice.
15. The system of claim 14, wherein the at least one row and the at least one column comprise qubit gates each comprising four qubits and qubit gates each comprising thirteen qubits, the qubit gates arranged alternately.
16. The system of claim 14, wherein the qubit gates of at least one row and/or at least one column comprise a plurality of qubit gates each comprising ten qubits.
17. The system of claim 14, wherein the qubit gates of at least one row and/or at least one column comprise a qubit gate comprising four qubits, a qubit gate comprising thirteen qubits, and/or a plurality of qubit gates each comprising ten qubits.
18. The system of claim 14, wherein the qubit gates comprise one of: equal numbers of qubit gates each comprising four qubits and qubit gates each comprising thirteen qubits, alternating with one another along each row and each column; or all of the qubit gates of the lattice comprising qubit gates each comprising ten qubits.
19. A quantum computing (QC) system comprising an array of three dimensional (3-D) gate cells each comprising multiple qubits.

20. The system of claim 19, the array comprising one or more gates each comprising nine qubits, gates each comprising eight qubits, and/or gates each comprising seven qubits.

21. The system of claim 1, wherein at least one of the one or more first qubits or the one or more second qubits comprise at least two qubits.
